

Paper is focused on finding an optimal annealing treatment for elimination of concentration of inclusions in (CdZn)Te. Demands for material used for MBE growth of (HgCd)Te are material without crystal imperfections, infrared transmittance above 60% and good crystalline quality. These parameters were measured by the X-ray diffraction rocking curve (XRC) method, Infrared Fourier Transform spectrometer and Infrared microscopy. The influence of annealing in the range of 600-850°C in Cd overpressure was investigated on samples contained Te-rich inclusions. The change of shape of Te-rich inclusions and infrared transmittance after annealing in Tellurium vapor was measured. The influence of annealing in Te overpressure in the range of 600-800°C was also investigated on samples contained Cd-rich inclusions, one sample was annealed in Cd overpressure.